

COMPLIANT



# Precision Monolithic Quad SPST Low-Voltage CMOS Analog Switches

#### **DESCRIPTION**

The DG411L, DG412L, DG413L are low voltage pin-for-pin compatible companion devices to the industry standard DG411, DG412, DG413 with improved performance.

Using BiCMOS wafer fabrication technology allows the DG411L, DG412L, DG413L to operate on single and dual supplies. Single supply voltage ranges from 3 to 12 V while dual supply operation is recommended with  $\pm$  3 to  $\pm$  6 V.

Combining high speed ( $t_{ON}$ : 19 ns), flat  $R_{DS(on)}$  over the analog signal range (5  $\Omega$ ), minimal insertion lose (- 3 dB at 280 MHz), and excellent crosstalk and off-isolation performance (- 50 dB at 50 MHz), the DG411L, DG412L, DG413L are ideally suited for audio and video signal switching.

The DG411L and DG412L respond to opposite control logic as shown in the Truth Table. The DG413L has two normally open and two normally closed switches.

#### **FEATURES**

- 2.7- thru 12 V single supply or ± 3- thru ± 6 dual supply
- On-resistance  $R_{DS(on)}$ : 17  $\Omega$
- Fast switching t<sub>ON</sub>: 19 ns
- t<sub>OFF</sub>: 12 ns
- TTL, CMOS compatible
- Low leakage: 0.25 nA
- 2000 V ESD protection

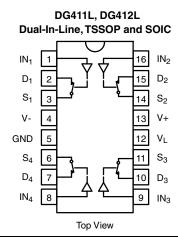
#### **BENEFITS**

- Widest dynamic range
- · Low signal errors and distortion
- · Break-before-make switching action
- Simple interfacinge

#### **APPLICATIONS**

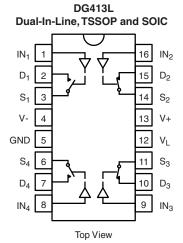
- · Precision automatic test equipment
- · Precision data acquisition
- Communication systems
- Battery powered systems
- Computer peripherals
- SDSL, DSLAM
- Audio and video signal routing

#### **FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION**



TRUTH TABLE						
Logic	DG411L	DG412L				
0	ON	OFF				
1	OFF	ON				

Logic "0"  $\leq$  0.8 V Logic "1"  $\geq$  2.4 V



TRUTH TABLE						
Logic	SW <sub>1</sub> , SW <sub>4</sub>	SW <sub>2</sub> , SW <sub>3</sub>				
0	OFF	ON				
1	ON	OFF				

 $\label{eq:logic "0" leq 0.8 V} \begin{tabular}{l} Logic "0" \le 0.8 \ V \\ Logic "1" \ge 2.4 \ V \end{tabular}$ 

<sup>\*</sup> Pb containing terminations are not RoHS compliant, exemptions may apply

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ORDERING INFORMATION					
Temp. Range	Package	Part Number			
DG411L, DG412L					
	16-Pin Narrow SOIC	DG411LDY DG411LDY-E3 DG411LDY-T1 DG411LDY-T1-E3			
- 40 °C to 85 °C	16-PIN Narrow SOIC	DG412LDY DG412LDY-E3 DG412LDY-T1 DG412LDY-T1-E3			
	16-Pin TSSOP	DG411LDQ DG411LDQ-E3 DG411LDQ-T1 DG411LDQ-T1-E3			
	10-FIII 1330F	DG412LDQ DG412LDQ-E3 DG412LDQ-T1 DG412LDQ-T1-E3			
DG413L	•				
- 40 °C to 85 °C	16-Pin Narrow SOIC	DG413LDY DG413LDY-E3 DG413LDY-T1 DG413LDY-T1-E3			
	16-Pin TSSOP	DG413LDQ DG413LDQ-E3 DG413LDQ-T1 DG413LDQ-T1-E3			

ABSOLUTE MAXIMUM RA	TINGS			
Parameter		Limit	Unit	
V+ to V-		- 0.3 to 13		
GND to V-		7		
V <sub>L</sub>		(GND - 0.3) to (V+) + 0.3	V	
$I_N^a, V_S, V_D$		- 0.3 to (V+) + 0.3 or 30 mA, whichever occurs first		
Continuous Current (Any terminal)		30	A	
Peak Current, S or D (Pulsed 1 ms, 10 9	% duty cycle)	100	mA	
Storage Temperature	(DQ, DY Suffix)	- 65 to 125	°C	
Storage remperature	(AK Suffix)	- 65 to 150	7 ~	
	16-Pin TSSOP <sup>c</sup>	450		
Power Dissipation (Packages) <sup>b</sup>	16-Pin SOIC <sup>d</sup>	650	mW	
	16-Pin CerDIP <sup>e</sup>	900		

- a. Signals on  $S_X$ ,  $D_X$ , or  $IN_X$  exceeding V+ or V- will be clamped by internal diodes. Limit forward diode current to maximum current ratings. b. All leads welded or soldered to PC board.
- c. Derate 7 mW/°C above 75 °C
- d. Derate 7.6 mW/°C above 75 °C
- e. Derate 12 mW/°C above 75 °C.



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SPECIFICATIONS <sup>a</sup> (	Single Sup	oply 12 V)							
		Test Conditions Unless Otherwise Specified			A Suffix Limits - 55 °C to 125 °C		D Suffix Limits - 40 °C to 85 °C		
Parameter	Symbol	$V_{+} = 12 V, V_{-} = 0 V$ $V_{L} = 5 V, V_{IN} = 2.4 V, 0.8 V^{f}$	Temp.b	Typ. <sup>c</sup>	Min.d	Max. <sup>d</sup>	Min.d	Max. <sup>d</sup>	Unit
Analog Switch									
Analog Signal Range <sup>e</sup>	V <sub>ANALOG</sub>		Full		0	12	0	12	V
Drain-Source On-Resistance	R <sub>DS(on)</sub>	V+ = 10.8  V, V- = 0  V $I_S = 10 \text{ mA}, V_D = 2/9 \text{ V}$	Room Full	20		30 45		30 40	Ω
Switch Off Leakage Current	I <sub>S(off)</sub>	V <sub>D</sub> = 1/11 V, V <sub>S</sub> = 11/1 V	Room Full		- 1 - 15	1 15	- 1 - 10	1 10	
•	I <sub>D(off)</sub>	VD = 1/11 V, VS = 11/1 V	Room Full		- 1 - 15	1 15	- 1 - 10	1 10	nA
Channel On Leakage Current	I <sub>D(on)</sub>	$V_{S} = V_{D} = 11/1 V$	Room Full		- 1 - 15	1 15	- 1 - 10	1 10	
Digital Control									
Input Current, V <sub>IN</sub> Low	I <sub>IL</sub>	V <sub>IN</sub> under test = 0.8 V	Full	0.01	- 1.5	1.5	- 1	1	μA
Input Current, V <sub>IN</sub> High	I <sub>IH</sub>	V <sub>IN</sub> under test = 2.4 V	Full		- 1.5	1.5	- 1	1	μΑ
Dynamic Characteristics									
Turn-On Time	$t_{ON}$	$R_L = 300 \Omega$ , $C_L = 35 pF$	Room Full	20		50 70		50 60	İ
Turn-Off Time	t <sub>OFF</sub>	$V_S = 5 V$ , see figure 2	Room Full	12		30 48		30 40	ns
Break-Before-Make Time Delay	t <sub>D</sub>	DG413L only, $V_S = 5 \text{ V}$ $R_L = 300 \Omega$ , $C_L = 35 \text{ pF}$	Room	6					
Charge Injection <sup>e</sup>	Q	$V_{q} = 0 \text{ V}, R_{q} = 0 \Omega, C_{L} = 10 \text{ nF}$	Room	5					рC
Off-Isolation <sup>e</sup>	OIRR		Room	71					
Channel-to-Channel Crosstalk <sup>e</sup>	X <sub>TALK</sub>	$R_L = 50 \Omega, C_L = 5 pF, f = 1 MHz$	Room	95					dB
Source Off Capacitance <sup>e</sup>	C <sub>S(off)</sub>		Room	5					
Drain Off Capacitance <sup>e</sup>	$C_{D(off)}$	f = 1 MHz	Room	6					pF
Channel-On Capacitance <sup>e</sup>	$C_{D(on)}$		Room	15					
Power Supplies									
Positive Supply Current	l+		Room Full	0.02		1 7.5		1 5	
Negative Supply Current	I-	V <sub>IN</sub> = 0 or 5 V	Room Full	- 0.002	- 1 - 7.5		- 1 - 5		
Logic Supply Current	Ι <sub>L</sub>	V <sub>IN</sub> = 0 01 3 V	Room Full	0.002		1 7.5		1 5	μΑ
Ground Current	I <sub>GND</sub>		Room Full	- 0.002	- 1 - 7.5		- 1 - 5		

- a. Refer to PROCESS OPTION FLOWCHART.
- b. Room = 25 °C, Full = as determined by the operating temperature suffix.
- c. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.
- d. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
- e. Guaranteed by design, not subject to production test.
- f.  $V_{IN}$  = input voltage to perform proper function.
- g. Leakage parameters are guaranteed by worst case test conditions and not subject to test.

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	Dual Supp	Test Conditions Unless Otherwise Specified			A Suffix Limits - 55 °C to 125 °C				
Parameter	Symbol	V+ = 5 V, V- = -5 V $V_L = 5 V, V_{IN} = 2.4 V, 0.8 V^f$	Temp.b	Ty.p <sup>c</sup>	Min.d	Max.d	Min.d	Max.d	Unit
Analog Switch			l .		I.	I.	I.		
Analog Signal Range <sup>e</sup>	V <sub>ANALOG</sub>		Full		- 5	5	- 5	5	V
Drain-Source On-Resistance	R <sub>DS(on)</sub>	V+ = 5 V, V- = -5 V $I_S = 10 \text{ mA}, V_D = \pm 3.5 V$	Room Full	20		33 45		33 40	Ω
Switch Off	I <sub>S(off)</sub>	V+ = 5.5 , V- = - 5.5 V	Room Full		- 1 - 15	1 15	- 1 - 10	1 10	
Leakage Current <sup>g</sup>	I <sub>D(off)</sub>	$V_D = \pm 4.5 \text{ V}, V_S = \pm 4.5 \text{ V}$	Room Full		- 1 - 15	1 15	- 1 - 10	1 10	nA
Channel On Leakage Current <sup>g</sup>	I <sub>D(on)</sub>	V+ = 5.5  V, V- = -5.5  V $V_S = V_D = \pm 4.5 \text{ V}$	Room Full		- 1 - 15	1 15	- 1 - 10	1 10	
Digital Control									
Input Current, V <sub>IN</sub> Low <sup>e</sup>	I <sub>IL</sub>	V <sub>IN</sub> under test = 0.8 V	Full	0.05	- 1.5	1.5	- 1	1	
Input Current, V <sub>IN</sub> High <sup>e</sup>	I <sub>IH</sub>	V <sub>IN</sub> under test = 2.4 V	Full	0.05	- 1.5	1.5	- 1	1	μΑ
Dynamic Characteristics									
Turn-On Time <sup>e</sup>	t <sub>ON</sub>	$R_L = 300 \Omega$ , $C_L = 35 pF$	Room Full	21		50 70		50 60	
Turn-Off Time <sup>e</sup>	t <sub>OFF</sub>	$V_S = \pm 3.5 \text{ V, see figure 2}$	Room Full	16		35 50		35 40	ns
Break-Before-Make Time Delay <sup>e</sup>	t <sub>D</sub>	DG413L only, $V_S = 3.5 \text{ V}$ $R_L = 300 \Omega$ , $C_L = 35 \text{ pF}$	Room	6					
Charge Injection <sup>e</sup>	Q	$V_{g} = 0 \text{ V}, R_{g} = 0 \Omega, C_{L} = 10 \text{ nF}$	Room	5					рС
Off Isolation <sup>e</sup>	OIRR		Room	68					
Channel-to-Channel Crosstalk <sup>e</sup>	X <sub>TALK</sub>	$R_L = 50 \Omega$ , $C_L = 5 pF$ , $f = 1 MHz$	Room	85					dB
Source Off Capacitance <sup>e</sup>	C <sub>S(off)</sub>		Room	9					
Drain Off Capacitance <sup>e</sup>	$C_{D(off)}$	f = 1 MHz	Room	9					pF
Channel On Capacitance <sup>e</sup>	$C_{D(on)}$		Room	20					
Power Supplies									
Positive Supply Current <sup>e</sup>	l+		Room Full	0.03		1 7.5		1 5	
Negative Supply Current <sup>e</sup>	<b> -</b>	V <sub>IN</sub> = 0 or 5 V	Room Full	- 0.002	- 1 - 7.5		- 1 - 5		
Logic Supply Current <sup>e</sup>	ال	v <sub>IN</sub> = 0 01 5 v	Room Full	0.002		1 7.5		1 5	μΑ
Ground Current <sup>e</sup>	I <sub>GND</sub>		Room Full	- 0.002	- 1 - 7.5		- 1 - 5		

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- d. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
- e. Guaranteed by design, not subject to production test.
- f.  $V_{IN}$  = input voltage to perform proper function.
- g. Leakage parameters are guaranteed by worst case test conditions and not subject to test.



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SPECIFICATIONS <sup>a</sup> (Single Supply 5 V)									
		Test Conditions Unless Otherwise Specified			A Suffix Limits - 55 °C to 125 °C		D Suffix Limits - 40 °C to 85 °C		
Parameter	Symbol	V+ = 5 V, V- = 0 V $V_L = 5 V, V_{IN} = 2.4 V, 0.8 V^f$	Temp.b	Typ. <sup>c</sup>	Min.d	Max. <sup>d</sup>	Min.d	Max. <sup>d</sup>	Unit
Analog Switch			•	l .	l .	I.		I.	
Analog Signal Range <sup>e</sup>	V <sub>ANALOG</sub>		Full			5		5	V
Drain-Source On-Resistance <sup>e</sup>	R <sub>DS(on)</sub>	V+ = 4.5 V $I_S = 5 \text{ mA}, V_D = 1 V, 3.5 V$	Room Full	35		50 88		50 75	Ω
Dynamic Characteristics									
Turn-On Time <sup>e</sup>	t <sub>ON</sub>	$R_L = 300 \Omega$ , $C_L = 35 pF$	Room Hot	27		50 90		50 60	
Turn-Off Time <sup>e</sup>	t <sub>OFF</sub>	$V_S = 3.5 V$ , see figure 2	Room Hot	15		30 55		30 40	ns
Break-Before-Make Time Delay <sup>e</sup>	t <sub>D</sub>	DG413L only, $V_S = 3.5 \text{ V}$ $R_L = 300 \Omega$ , $C_L = 35 \text{ pF}$	Room	6					
Charge Injection <sup>e</sup>	Q	$V_{g} = 0 \text{ V}, R_{g} = 0 \Omega, C_{L} = 10 \text{ nF}$	Room	0.5					рС
Power Supplies									
Positive Supply Current <sup>e</sup>	l+		Room Hot	0.02		1 7.5		1 5	
Negative Supply Current <sup>e</sup>	l-	V 0 27 5 V	Room Hot	- 0.002	- 1 - 7.5		- 1 - 5		
Logic Supply Current <sup>e</sup>	ΙL	V <sub>IN</sub> = 0 or 5 V	Room Hot	0.002		1 7.5		1 5	μΑ
Ground Current <sup>e</sup>	I <sub>GND</sub>		Room Hot	- 0.002	- 1 - 7.5		- 1 - 5		

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- b. Room = 25  $^{\circ}\text{C}$ , Full = as determined by the operating temperature suffix.
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- e. Guaranteed by design, not subject to production test.
- f.  $V_{IN}$  = input voltage to perform proper function.
- g. Leakage parameters are guaranteed by worst case test conditions and not subject to test.

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SPECIFICATIONS <sup>a</sup>	(Single Su	oply 3 V)							
		Test Conditions Unless Otherwise Specified			A Suffix Limits - 55 °C to 125 °C			k Limits to 85 °C	
Parameter	Symbol	$V_{+} = 3 V, V_{-} = 0 V$ $V_{L} = 3 V, V_{IN} = 0.4 V^{f}$	Temp.b	Typ. <sup>c</sup>	Min.d	Max. <sup>d</sup>	Min. <sup>d</sup>	Max. <sup>d</sup>	Unit
Analog Switch									
Analog Signal Range <sup>e</sup>	V <sub>ANALOG</sub>		Full		0	3	0	3	V
Drain-Source On-Resistance	R <sub>DS(on)</sub>	V+ = 2.7  V, V- = 0  V $I_S = 5 \text{ mA}, V_D = 0.5, 2.2 \text{ V}$	Room Full	65		80 115		80 100	Ω
Switch Off	I <sub>S(off)</sub>	V+ = 3.3 , V- = 0 V	Room Full		- 1 - 15	1 15	- 1 - 10	1 10	
Leakage Current <sup>g</sup>	I <sub>D(off)</sub>	$V_D = 1, 2 V, V_S = 2, 1 V$	Room Full		- 1 - 15	1 15	- 1 - 10	1 10	nA
Channel On Leakage Current <sup>g</sup>	I <sub>D(on)</sub>	$V_{+} = 3.3 \text{ V}, V_{-} = 0 \text{ V}$ $V_{S} = V_{D} = 1, 2 \text{ V}$			- 1 - 15	1 15	- 1 - 10	1 10	
Digital Control									
Input Current, V <sub>IN</sub> Low	I <sub>IL</sub>	V <sub>IN</sub> under test = 0.4 V	Full	0.005	- 1.5	1.5	- 1	1	μΑ
Input Current, V <sub>IN</sub> High	I <sub>IH</sub>	V <sub>IN</sub> under test = 2.4 V	Full	0.005	- 1.5	1.5	- 1	1	μΛ
Dynamic Characteristics									
Turn-On Time	t <sub>ON</sub>	$R_L = 300 \Omega$ , $C_L = 35 pF$	Room Full	50		85 150		85 110	
Turn-Off Time	t <sub>OFF</sub>	$V_S = 1.5 \text{ V}$ , see figure 2	Room Full	30		60 100		60 85	ns
Break-Before-Make Time Delay	t <sub>D</sub>	DG413L only, $V_S = 1.5 \text{ V}$ $R_L = 300 \Omega$ , $C_L = 35 \text{ pF}$	Room	6					
Charge Injection <sup>e</sup>	Q	$V_g = 0 \text{ V, } R_g = 0 \Omega, C_L = 10 \text{ nF}$	Room	1					рC
Off Isolation <sup>e</sup>	OIRR		Room	68					
Channel-to-Channel Crosstalk <sup>e</sup>	X <sub>TALK</sub>	$R_L$ = 50 Ω, $C_L$ = 5 pF , f = 1 MHz	Room	85					dB
Source Off Capacitance <sup>e</sup>	C <sub>S(off)</sub>		Room	6					
Drain Off Capacitance <sup>e</sup>	C <sub>D(off)</sub>	f = 1 MHz	Room	6					pF
Channel On Capacitance <sup>e</sup>	C <sub>D(on)</sub>		Room	20					

#### Notes

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- f.  $V_{IN}$  = input voltage to perform proper function.
- g. Leakage parameters are guaranteed by worst case test conditions and not subject to test.

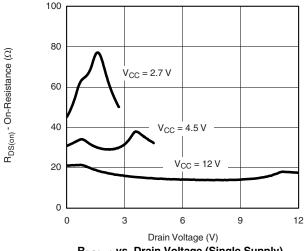
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



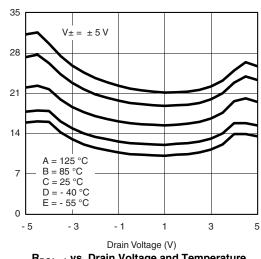
 $\mathsf{R}_{\mathsf{DS}(\mathsf{on})}$  - On-Resistance  $(\Omega)$ 

I<sub>S</sub> , I<sub>D</sub> Leakage Current (pA)

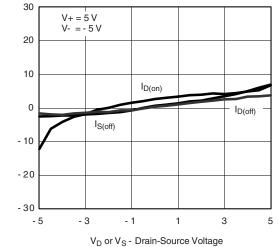
#### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



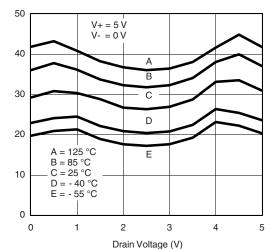
R<sub>DS(on)</sub> vs. Drain Voltage (Single Supply)



R<sub>DS(on)</sub> vs. Drain Voltage and Temperature (Dual Supply)



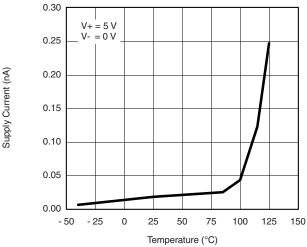
Leakage Current vs. Analog Voltage (Dual Supply)



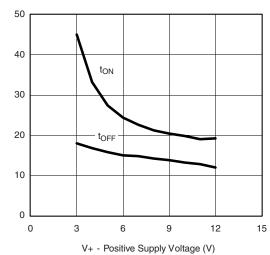
 $\mathsf{R}_{\mathsf{DS}(\mathsf{on})}$  - On-Resistance  $(\Omega)$ 

Switching Speed (nS)

R<sub>DS(on)</sub> vs. Drain Voltage and Temperature (Single Supply)



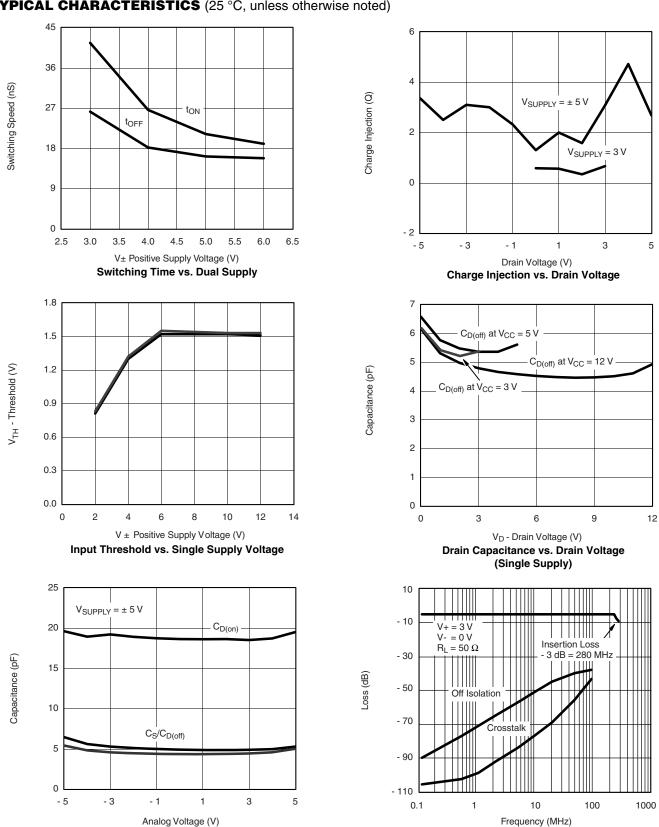
Supply Current vs. Temperature



Switching Time vs. Single Supply

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#### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Capacitance vs. Analog Signal

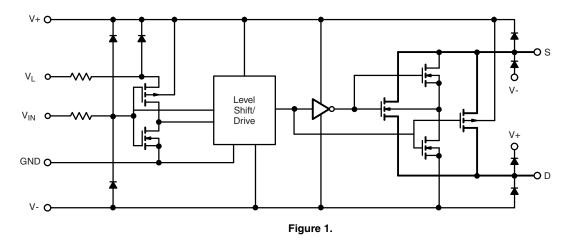
(Dual Supply)

Insertion Loss, Off Isolation and Crosstalk

vs. Frequency (Single Supply)



#### **SCHEMATIC DIAGRAM** (Typical Channel)



#### **TEST CIRCUITS**

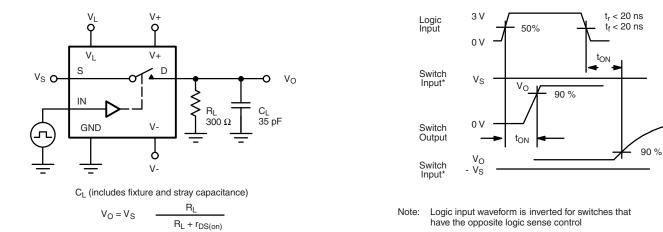


Figure 2. Switching Time

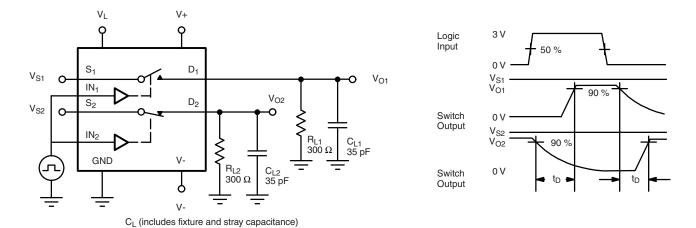
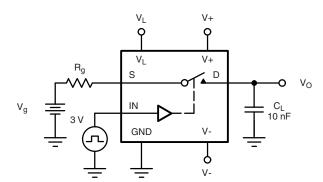


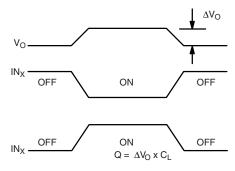
Figure 3. Break-Before-Make (DG413L)

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#### **TEST CIRCUITS**







 $\ensuremath{\mathsf{IN}}_X$  dependent on switch configuration Input polarity determined by sense of switch.

Figure 4. Charge Injection

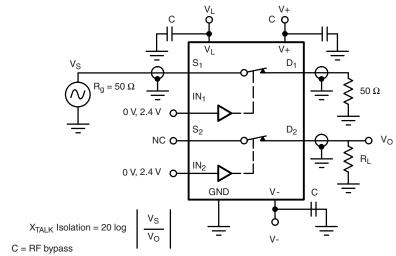
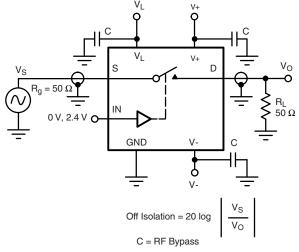


Figure 5. Crosstalk





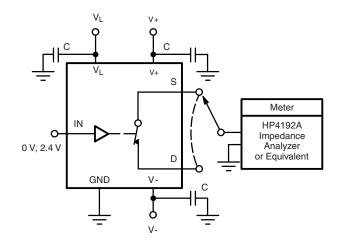


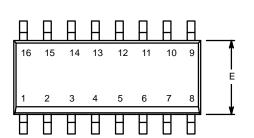
Figure 7. Source/Drain Capacitances

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg?71397">www.vishay.com/ppg?71397</a>.





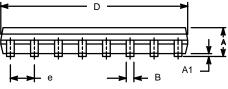
SOIC (NARROW): 16-LEAD JEDEC Part Number: MS-012

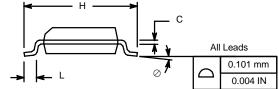


	MILLIM	MILLIMETERS		HES		
Dim	Min	Max	Min	Max		
Α	1.35	1.75	0.053	0.069		
A <sub>1</sub>	0.10	0.20	0.004	0.008		
В	0.38	0.51	0.015	0.020		
С	0.18	0.23	0.007	0.009		
D	9.80	10.00	0.385	0.393		
E	3.80	4.00	0.149	0.157		
е	1.27	BSC	0.050	BSC		
Н	5.80	6.20	0.228	0.244		
L	0.50	0.93	0.020	0.037		
0	0°	8°	0°	8°		
FCN: S-03946—Rev. F. 09-Jul-01						

ECN: S-03946—Rev. F, 09-Jul-01

DWG: 5300

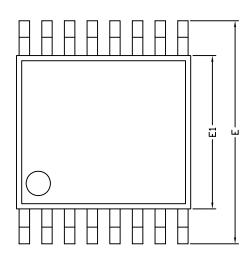


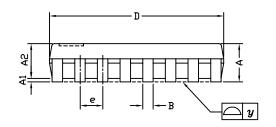


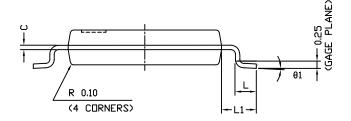
www.vishay.com 02-Jul-01



**TSSOP: 16-LEAD** 







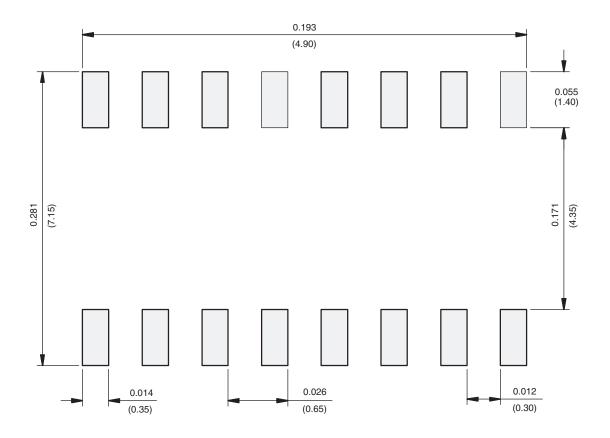
	DIMENSIONS IN MILLIMETERS						
Symbols	Min	Nom	Max				
А	=	1.10	1.20				
A1	0.05	0.10	0.15				
A2	=	1.00	1.05				
В	0.22	0.28	0.38				
С	=	0.127	-				
D	4.90	5.00	5.10				
E	6.10	6.40	6.70				
E1	4.30	4.40	4.50				
е	-	0.65	-				
L	0.50	0.60	0.70				
L1	0.90	1.00	1.10				
у	=	-	0.10				
θ1	0°	3°	6°				
ECN: S-61920-Rev. D. 23-0	Oct-06	<u> </u>					

DWG: 5624

Document Number: 74417 www.vishay.com 23-Oct-06



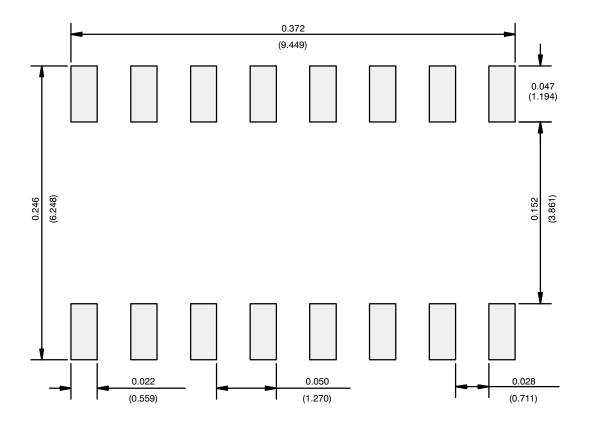
#### **RECOMMENDED MINIMUM PAD FOR TSSOP-16**



Recommended Minimum Pads Dimensions in inches (mm)



#### **RECOMMENDED MINIMUM PADS FOR SO-16**



Recommended Minimum Pads Dimensions in Inches/(mm)

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Revision: 02-Oct-12 Document Number: 91000